PECLERS[®]

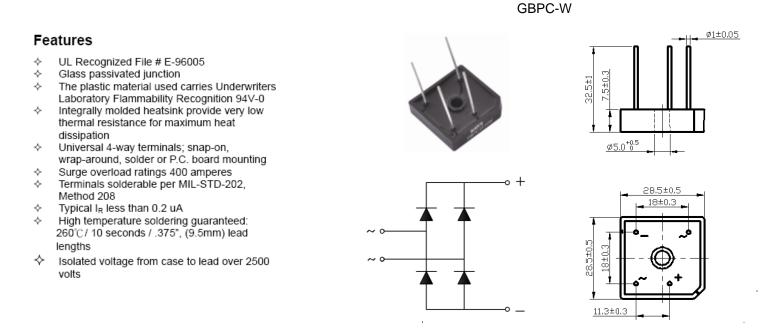
GBPC50005W Thru GBPC5010W

Dimensions in millimeters

HIGH CURRENT SINGLE-PHASE SILICON BRIDGE RECTIFIER

REVERSE VOLTAGE: FORWARD CURRENT:

50 to 1000 VOLTS



50 AMPERE

Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60H₇, resistive or inductive load.

For capacitive load, derate current by 20%.

	Symbols	005	01	02	04	06	08	10	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Current at TC=55℃	I _(AV)	50							Amp
Peak Forward Surge Current,8.3ms single half-sine- wave superimposed on rated load (JEDEC method)	I _{FSM}	450							Amp
Maximum Forward Voltage at 25A DC and 25°C	V _F	1.1							Volts
Maximum Reverse Currentat T_A=25°Cat Rated DC Blocking VoltageT_A=125°C	I _R	10.0 1000							uAmp
Typical Junction Capacitance (Note 1)	CJ	300							pF
Typical Thermal Resistance (Note 2)	R _{0JC}	2							°C/W
Operating and Storage Temperature Range	T _J , Tstg	-55 to +150							Ĉ

NOTES:

1- Measured at 1 MHz and applied reverse voltage of 4.0 VDC.

2- Thermal resistance from junction to case per leg

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RATINGS AND CHARACTERISTIC CURVES

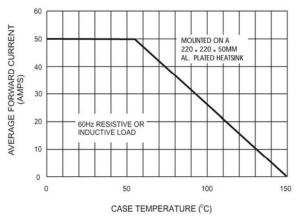


Figure 1. Forward Current Derating Curve

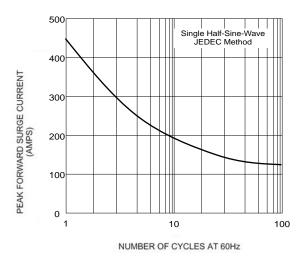


Figure 3. Maximum Non-repetitive Peak Forward Surge Current Per Bridge Element

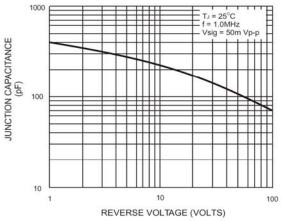
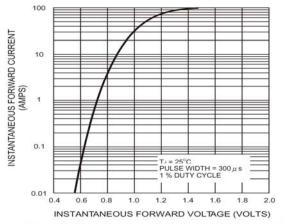


Figure 5. Typical Junction Capacitance Per Bridge Element





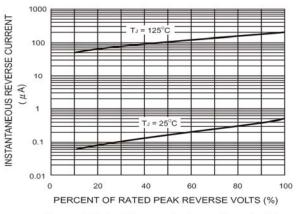


Figure 4. Typical Reverse Leakage Characteristics Per Bridge Element

